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(54) Title: METHOD FOR FORMING Si-CONTAINING FILM

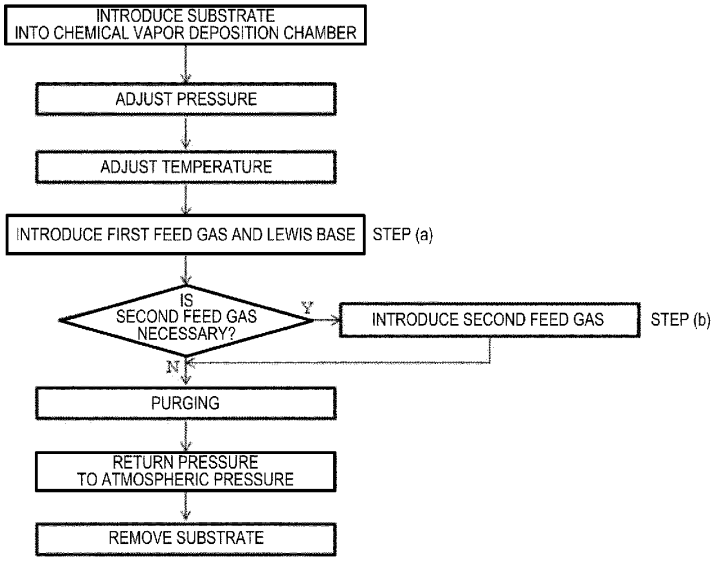

FIG.2

(57) Abstract: To provide a deposition process whereby a seamless Si-containing film having a small number of voids can be formed on a substrate having a fine trench at a lower temperature. A method for forming an Si-containing film forms an Si-containing film on a substrate by a chemical vapor deposition process, wherein the chemical vapor deposition process includes a step (a) that reacts a first feed gas having one or more Si-Si bonds in a chemical vapor deposition chamber in the presence of a Lewis base catalyst.

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